

ABSTRACT

ELECTRONIC DEVICES COMPRISING THIN FILM TRANSISTORS

5 The invention provides a method of manufacturing an electronic device including a vertical thin film transistor. A layer (8) of semiconductor material is provided over an insulated gate electrode (2). A negative resist (14) is used to define source and drain electrodes (26,28) which extend over the insulating layer (8) up to the step formed therein adjacent an edge (16A) of the gate electrode (2).

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[Figure 2]